



1/25/2008

**RELIABILITY MONITOR REPORT  
FOR**

**SAT 0.8 $\mu$ m Silicon Gate CMOS w/memory**

**MAXIM Integrated Products**

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Sunnyvale, CA 94086

**This Report was prepared by  
Maxim Reliability Engineering**

**Summary:**

The data in the tables that follow was generated as the result of an on-going Process Reliability Monitor. The specific products in this process monitor are:

MAX1781ETM+	MAX1783EPM
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The calculated failure rate for devices using this process is:

**FAILURE RATE:**                      **MTTF (YRS): 44764**                      **FITS: 2.6**

The parameters used to calculate this failure rate are as follows:

**Cf: 60%**                      **Ea: 0.7**                      **Tu: 25 °C**

The reliability data follows and in this section is the detailed reliability data by stress. The reliability data section includes the latest data available. This report covers data between and .

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**Process Information:**

Process Description:                      SAT 0.8µm Silicon Gate CMOS w/memory

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**OPERATING LIFE**

DESCRIPTION	DATE CODE	TEST VEHICLE	CONDITION	READPOINT	QUANTITY	FAILS	FA NO
HIGH TEMP OP LIFE	0604	MAX1781ETM+	135C, 5.25V	1000 HRS	77	0	
HIGH TEMP OP LIFE	0621	MAX1783EPM	135C, 5.25V	1000 HRS	77	0	
			135C, 5.25V	1000 HRS	77	0	
				<b>Total:</b>		<b>0</b>	

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